

## DZ4J180K0R

## Silicon epitaxial planar type

For constant voltage / For surge absorption circuit

### ■ Features

- Excellent rising characteristics of zener current  $I_Z$
- Low zener operating resistance  $R_Z$
- Halogen-free / RoHS compliant  
(EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)

### ■ Marking Symbol: YJ

### ■ Basic Part Number :

Dual DZ2J180 (Parallel)

### ■ Packaging

Embossed type (Thermo-compression sealing) 3 000 pcs / reel (standard)

### ■ Absolute Maximum Ratings $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Repetitive peak forward current	IFRM	200	mA
Total power dissipation <sup>*1</sup>	PT	200	mW
Electrostatic discharge <sup>*2</sup>	ESD	±8	kV
Junction temperature	Tj	150	°C
Operating ambient temperature	Topr	-40 to +85	°C
Storage temperature	Tstg	-55 to +150	°C

Note) \*1: Mounted on glass epoxy print board. (45 mm x 45 mm x 1 mm)

Solder in (0.8 mm x 0.8 mm)

\*2: Test method: IEC61000\_4\_2(C = 150 pF, R = 330 Ω, Contact discharge: 10 times)

### ■ Electrical Characteristics $T_a = 25\text{ }^\circ\text{C} \pm 3\text{ }^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward voltage	VF	IF = 10 mA			1.0	V
Zener voltage <sup>*1, *2</sup>	VZ	IZ = 5 mA	17.10		18.90	V
Zener operating resistance	RZ	IZ = 5 mA			60	Ω
Zener rise operating resistance	RZK	IZ = 0.5 mA			80	Ω
Reverse current	IR	VR = 13 V			0.05	μA
Temperature coefficient of zener voltage <sup>*3</sup>	SZ	IZ = 5 mA		17.2		mV/°C

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 Measuring methods for Diodes.

2. Absolute frequency of input and output is 5 MHz.

3. \*1: The temperature must be controlled 25 °C for VZ measurement.

VZ value measured at other temperature must be adjusted to VZ (25 °C)

\*2: VZ guaranteed 20 ms after current flow.

\*3: Tj = 25 °C to 150 °C

